

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Vishay/Siliconix DG9414DQ-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com





Vishay Siliconix

Single 4 x 1 and Dual 2 x 1 Multiplexers

DESCRIPTION

The DG9414, a single 4 to 1 multiplexer, and the DG9415, a dual 2 x 1 multiplexer, are monolithic CMOS analog devices designed for high performance low voltage operation. Combining low power, high speed, low on-resistance and small physical size, the DG9414 and DG9415 are ideal for portable and battery powered applications requiring high performance and efficient use of board space.

Both the DG9414 and DG9415 are built on Vishay Siliconix's low voltage BCD-15 process. Minimum ESD protection, per Method 3015.7, is 2000 V. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG9415.

FEATURES

- Low voltage operation (+ 2.7 V to + 12 V)
- Low on-resistance R_{DS}(on): 14 Ω
- Low power consumption
- TTL compatible
- ESD protection > 2000 V (method 3015.7)
- Available in TSSOP-10 (aka MSOP-10)
- Compliant to RoHS Directive 2002/95/EC

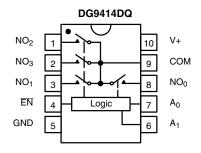
BENEFITS

- · High accuracy
- Simple logic interface
- Reduce board space

APPLICATIONS

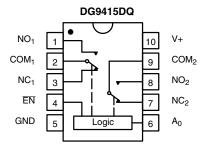
- · Battery operated systems
- · Portable test equipment
- · Sample and hold circuits
- Cellular phones
- Communication systems
- Networking equipment

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



EN	A ₁	Α ₀	On Switch
1	Х	Х	None
0	0	0	NO ₀
0	0	1	NO ₁
0	1	0	NO ₂
0	1	1	NO ₃

X = Do not care



EN	A_0	On Switch
1	X	None
0	0	NC ₁ NC ₂
0	1	NO ₁ NO ₂

X = Do not care

ORDERING INFORMATION							
Temp Range	Package	Part Number					
- 40 °C to 85 °C	MSOP-10	DG9414DQ-T1-E3					
- 40 C to 65 C	WISOF-10	DG9415DQ-T1-E3					

Document Number: 71766 S11-0984-Rev. G, 23-May-11

Distributor of Vishay/Siliconix: Excellent Integrated System Limited

Datasheet of DG9414DQ-T1-E3 - IC MULTIPLEXER DUAL 4X1 10MSOP

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

DG9414, DG9415

Vishay Siliconix



ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Reference V+ to GND	- 0.3 to + 13	V				
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)	7 ·				
Continuous Current (Any terminal)	± 20	m A				
Peak Current (Pulsed at 1 ms, 10 % duty cycle)	± 40	mA				
ESD (Method 3015.7)	> 2000	V				
Storage Temperature (D Suffix)	- 65 to 150	°C				

a. Signals on S_X , D_X or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads soldered or welded to PC board.

D	0	Test Conditions Otherwise Unless Specified V+ = 3 V, \pm 10 %, V_{IN} = 0.4 V or 2.4 V^e			Limits - 40 °C to 85 °C			
Parameter	Symbol			Temp.a	Min.c	Typ.b	Max.c	Unit
Analog Switch								
Analog Signal Range ^d	V _{ANALOG}			Full	0		V+	V
On-Resistance	R _{ON}			Room Full		63	97 101	
R _{ON} Match ^d	ΔR _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 1 \text{ V}/1.5$ $I_{NO} \text{ or } I_{NC} = 5 \text{ mA}$	V/2 V	Room		3	11	Ω
R _{ON} Flatness ^{d,f}	R _{ON} Flatness	NO NO		Room		14	33	
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	$V+ = 3.3$, V_{NO} or $V_{NC} = 0.3$	V/3 V	Room Full	- 1 - 10		1 10	
COM Off Leakage Current ^g	I _{COM(off)}	$V_{COM} = 3 \text{ V}/0.3 \text{ V}$		Room Full	- 1 - 10		1 10	nA
Channel-On Leakage Current ^g	I _{COM(on)}	$V_{COM} = V_{NO} \text{ or } V_{NC} = 0.3 \text{ V/3 V}$		Room Full	- 1 - 10		1 10	
Digital Control								
Input Current ^g	I _{INL} or I _{INH}	$V_{IN} = 0$ or V+		Full	- 1		1	μΑ
Input High Voltage ^d	V_{INH}			Full	1.6			V
Input Low Voltage ^d	V_{INL}			Full			0.4	v
Dynamic Characteristics								
Turn-On Time	t _{ON}			Room Full		102	125 142	
Turn-Off Time	t _{OFF}	V_{NO} or $V_{NC} = 1.5 V$		Room Full		45	68 75	ns
Break-Before-Make Time	t _D			Room	7	78		
Transition Time	t _{trans}	V _{NO} = 1.5 V/0 V, V _{NC} = 0 V/	/1.5 V	Room Full		81	128 144	
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{gen} = 0 \text{ V, } R_{gen}$	= 0 Ω	Room		3		рС
Off-Isolation	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1$	MHz	Room		- 58		
Channel-to-Channel Crosstalk (DG9415)	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$		Room		- 64		dB
NO, NC Off Capacitance	C _{NO(off)} ,		DG9414	Room		11		
	C _{NC(off)}		DG9415	Room		10		
COM Off Capacitance	C _{COM(off)}	f = 1 MHz	DG9414 DG9415	Room Room		26 13		pF
COM On Capacitance	C _{COM(on)}	DG9414 DG9415		Room		43 25		1
Power Supply			1 2 40 1 10	. 100111			l	
Power Supply Range	V+				2.7		3.3	V
Power Supply Currenth	l+	V+ = 3.3 V, V _{IN} = 0 V or 3	.3 V	Full			1	μΑ

Distributor of Vishay/Siliconix: Excellent Integrated System Limited Datasheet of DG9414DQ-T1-E3 - IC MULTIPLEXER DUAL 4X1 10MSOP

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



DG9414, DG9415

Vishay Siliconix

Parameter	Symbol	Test Conditions Otherwise Unless Specified			Limits - 40 °C to 85 °C		°C	
		$V+ = 5 V$, $\pm 10 \%$, $V_{IN} = 0.8 V$	or 2.4 V ^e	Temp.a	Min. ^c	Typ.b	Max.c	Uni
Analog Switch								
Analog Signal Range ^d	V _{ANALOG}			Full	0		V+	V
On-Resistance	R _{ON}	V 45VV 45V/05V/05V		Room Full		33	56 60	
R _{ON} Match	ΔR_{ON}	$V+ = 4.5 \text{ V}, V_{COM} = 1.5 \text{ V}/2.5 \text{ V}$ $I_{NO} \text{ or } I_{NC} = 10 \text{ mA}$	V/3.5 V	Room		2	10	Ω
R _{ON} Flatness ^f	R _{ON} Flatness	INO SI INC = 19 III/I		Room		10	20	
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	$V+ = 5.5 V$, V_{NO} or $V_{NC} = 1 V$	/4.5 V	Room Full	- 1 - 10		1 10	
COM Off Leakage Current ^g	I _{COM(off)}	$V_{COM} = 4.5 \text{ V/1 V}$		Room Full	- 1 - 10		1 10	nA
Channel-On Leakage Current ^g	I _{COM(on)}	$V+ = 5.5 V$ $V_{COM} = V_{NO} \text{ or } V_{NC} = 1 \text{ V/4}$.5 V	Room Full	- 1 - 10		1 10	
Digital Control								
Input Currenth	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ or } V+$		Full	- 1		1	μΑ
Input High Voltage ^d	V _{INH}			Full	1.8			V
Input Low Voltage ^d	V_{INL}			Full			0.6	V
Dynamic Characteristics								
Turn-On Time ^h	t _{ON}			Room Full		56	77 86	
Turn-Off Time ^h	t _{OFF}	V_{NO} or $V_{NC} = 3 V$		Room Full		25	46 50	ns
Break-Before-Make Timet ^h	t _D			Room	7	34		
Transition Time	t _{trans}	$V_{NO} = 3 \text{ V/ } 0 \text{ V, } V_{NC} = 0 \text{ V/}$	3 V	Room Full		47	77 84	
Off-Isolation	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1$	MHz	Room		- 58		
Channel-to-Channel Crosstalk (DG9415)	X _{TALK}	$R_L = 50 \Omega$, $f = 1 MHz$		Room		- 64		dE
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{gen} = 0 \text{ V, } R_{gen} = 0 \text{ V}$	Ω 0 =	Room		6		рС
NO, NC Off Capacitance	$C_{NO(off)}$, $C_{NC(off)}$		DG9414 DG9415	Room Room		11 10		
COM Off Capacitance	C _{COM(off)}	f = 1 MHz	DG9414 DG9415	Room		25 13		рF
COM On Capacitance	C _{COM(on)}	DG9414 DG9415		Room		42		
Power Supply			DG3413	1100111		-4		
Power Supply Range	V+				4.5		5.5	V
Power Supply Current ^h	I+	V+ = 5.5 V, V _{IN} = 0 V or 5.5 V		Full			1	μΑ

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guaranteed by 12 V leakage testing, not production tested.
- h. Guaranteed by worst case test conditions and not subject to test.

Document Number: 71766 S11-0984-Rev. G, 23-May-11

Distributor of Vishay/Siliconix: Excellent Integrated System Limited Datasheet of DG9414DQ-T1-E3 - IC MULTIPLEXER DUAL 4X1 10MSOP

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

DG9414, DG9415

Vishay Siliconix



Parameter	Symbol	Test Conditions Unless Specified			Limits - 40 °C to 85 °C			
		$V+ = 12 \text{ V}, V_{1N} = 0.8 \text{ V or } 2$.4 V ^e	Temp.a	Min.c	Typ.b	Max.c	Unit
Analog Switch								
Analog Signal Range ^d	V _{ANALOG}			Full	0		12	V
R _{ON} Match	ΔR _{ON}			Room		1	9	
R _{ON} Flatness ^{d,f}	R _{ON} Flatness			Room		1	10	Ω
On-Resistance	R _{ON}	$V+ = 10.8 \text{ V}, I_{NO}, I_{NC} = 25$ $V_{COM} = 2/9 \text{ V}$	mA	Room Full		14	17 19	
Switch Off	I _{NO(off)} I _{NC(off)}	V _{COM} = 1/11 V		Room Full	- 1 - 10		1 10	
Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 11/1 V$		Room Full	- 1 - 10		1 10	nA
Channel On Leakage Current	I _{COM(on)}	$V_{NO}, V_{NC} = V_{COM} = 11/1 \text{ V}$		Room Full	- 1 - 10		1 10	<u> </u>
Digital Control	, , , , , , , , , , , , , , , , , , ,					1	1	
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ or } V+$		Full	- 1		1	μΑ
Input High Voltage ^d	V _{INH}			Full	2.4			V
Input Low Voltage ^d	V _{INL}			Full		0.8		
Dynamic Characteristics								
Turn-On Time ^h	t _{ON}	$R_L = 300 \ \Omega, \ C_L = 35 \ pl$		Room Full		33	55 59	
Turn-Off Time ^h	t _{OFF}	V _{NO} , V _{NC} = 5 V See Figu		Room Full		17	40 41	
Break-Before-Make Time Delay ^h	t _D	DG419L Only, V_{NC} , V_{NO} = $R_L = 300 \Omega$, $C_L = 35 pl$		Room	2	24		ns
Transition Time	t _{trans}	$V_{NO} = 5 \text{ V/ } 0 \text{ V}, V_{NC} = 0 \text{ V}$		Room Full		29	56 59	
Charge Injection ^d	Q _{INJ}	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1$	nF	Room		13		рC
Off Isolation ^d	OIRR	$R_L = 50 \Omega, C_L = 5 pF$		Room		- 58		٩D
Channel-to-Channel Crosstalk ^d	X _{TALK}	f = 1 MHz		Room		- 64		dB
NO, NC Off Capacitance ^d	$C_{NO(off)}$, $C_{NC(off)}$		DG9414 DG9415	Room Room		10 10		
COM Off Capacitance	C _{COM(off)}	$V_{IN} = 0$ or V+, f = 1 MHz	DG9414 DG9415	Room		24		рF
COM On Capacitance ^d	C _{COM(on)}	DG9413 DG9414 DG9415		Room		40		
Power Supplies			DG3413	HUUIII			<u> </u>	
Positive Supply Current	I+	V _{IN} = 0 V or 12 V		Full			1	μА

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guaranteed by 12 V leakage testing, not production tested.
- h. Guaranteed by worst case test conditions and not subject to test.

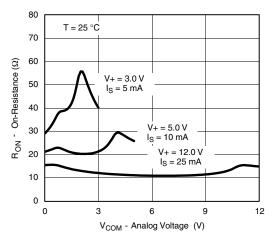
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



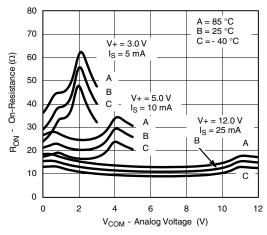


Vishay Siliconix

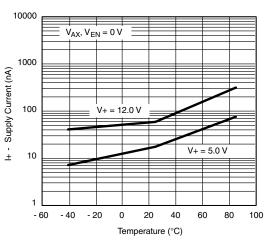
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



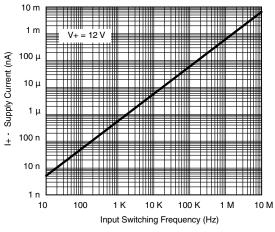
R_{ON} vs. V_{COM} and Supply Voltage



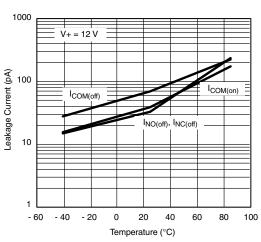
R_{ON} vs. Analog Voltage and Temperature



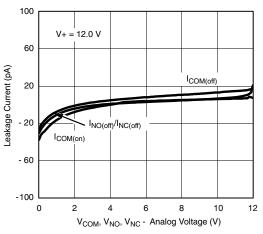
Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency



Leakage Current vs. Temperature



Leakage vs. Analog Voltage

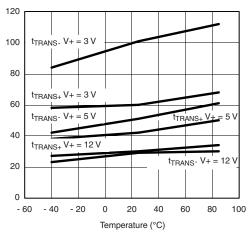
Document Number: 71766 S11-0984-Rev. G, 23-May-11



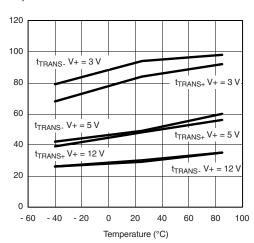
Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

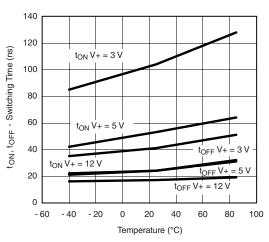




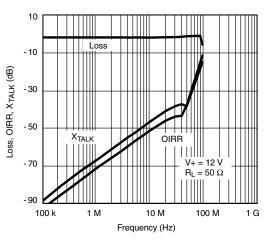
Transistion Time vs. Temperature (DG9414)



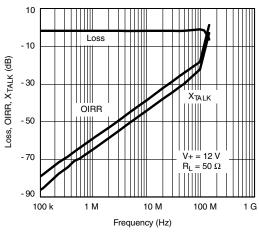
Transistion Time vs. Temperature (DG9415)



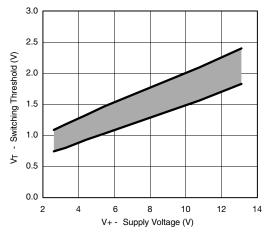
Switching Time vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency (DG9414)



Insertion Loss, Off-Isolation Crosstalk vs. Frequency (DG9415)



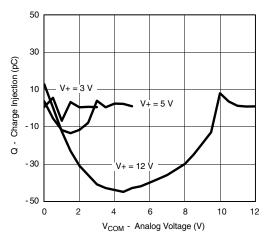
Switching Threshold vs. Supply Voltage



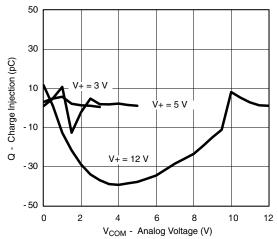


Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

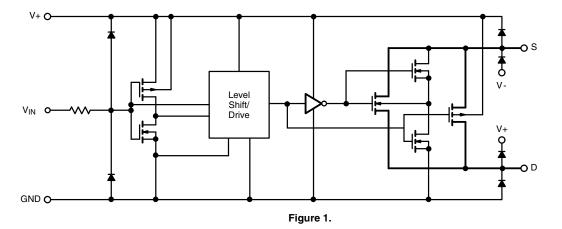


Charge Injection vs. Analog Voltage (DG9414)

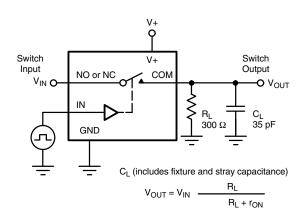


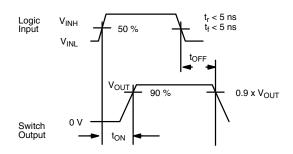
Charge Injection vs. Analog Voltage (DG9415)

SCHEMATIC DIAGRAM (Typical Channel)



TEST CIRCUITS





Logic input waveform is inverted for switches that Note: have the opposite logic sense control

Figure 2. Switching Time

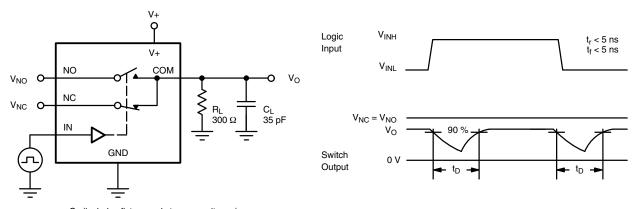
Document Number: 71766 S11-0984-Rev. G, 23-May-11



Vishay Siliconix

TEST CIRCUITS





C_L (includes fixture and stray capacitance)

Figure 3. Break-Before-Make

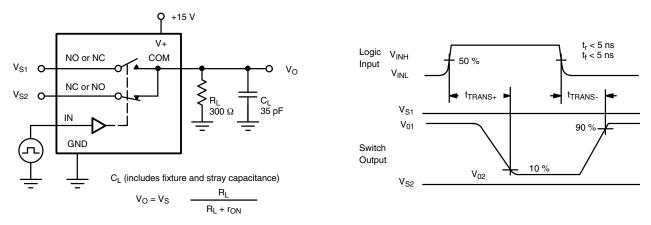


Figure 4. Transition Time

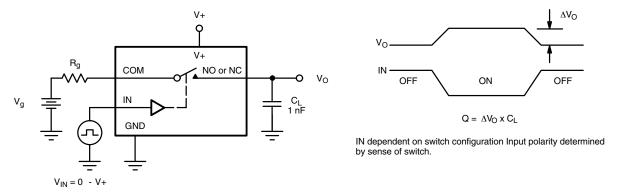


Figure 5. Charge Injection





Vishay Siliconix

TEST CIRCUITS

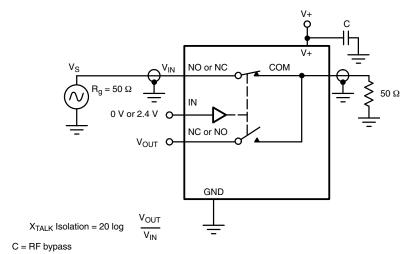


Figure 6. Crosstalk

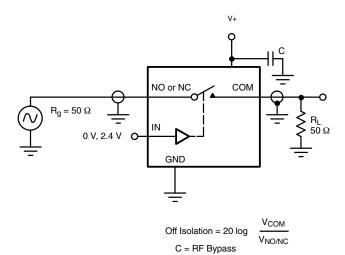


Figure 7. Off Isolation

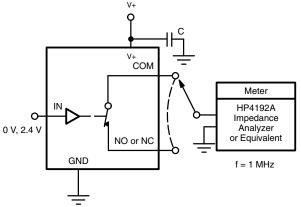


Figure 8. Source/Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71766.

Document Number: 71766 S11-0984-Rev. G, 23-May-11

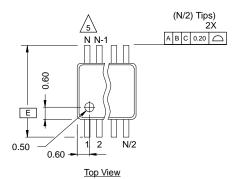


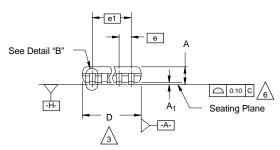


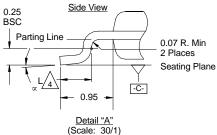
Package Information Vishay Siliconix

MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)









- Die thickness allowable is 0.203 ± 0.0127 .
- Dimensioning and tolerances per ANSI.Y14.5M-1994.



Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane -H-, mold flash or protrusions shall not exceed



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

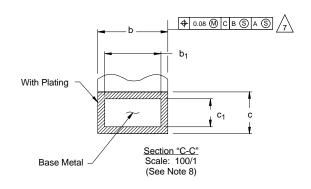
Controlling dimension: millimeters.

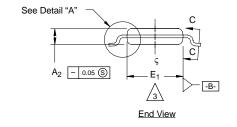
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

/11\ Datums -A- and -B- to be determined Datum plane -H-.

Exposed pad area in bottom side is the same as teh leadframe pad size.







N = 10L

	MI	MILLIMETERS				
Dim	Min	Nom	Max	Note		
Α	-	-	1.10			
A ₁	0.05	0.10	0.15			
A ₂	0.75	0.85	0.95			
b	0.17	-	0.27	8		
b ₁	0.17	0.20	0.23	8		
С	0.13	-	0.23			
c ₁	0.13	0.15	0.18			
D		3.00 BSC				
Е		4.90 BSC				
E ₁	2.90	3.00	3.10	3		
е		0.50 BSC				
e ₁		2.00 BSC				
L	0.40	0.55	0.70	4		
N		10				
œ	0°	4°	6°			
ECN: T-02 DWG: 58	2080—Rev. 0 67	C, 15-Jul-02				

Document Number: 71245 www.vishay.com 12-Jul-02



Distributor of Vishay/Siliconix: Excellent Integrated System Limited Datasheet of DG9414DQ-T1-E3 - IC MULTIPLEXER DUAL 4X1 10MSOP

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com





www.vishay.com

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000